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YO998426DIV

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of

Chan et al.

Serial No.: 10/051,562

Group Art Unit: 2822

Filed: January 18, 2002

Examiner: Novacek, Christy L.

For: SELF-ALIGNED DOUBLE-GATE MOSFET BY SELECTIVE EPITAXY  
AND SILICON WAFER BONDING TECHNIQUES

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

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SEP 25 2003

AMENDMENT UNDER 37 C.F.R. §1.116

OFFICIAL

Sir:

In response to the Office Action mailed July 23, 2003, please amend the above-identified patent application as follows:

IN THE CLAIMS:

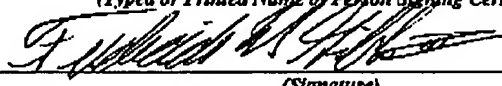
Please cancel claim 36 and amend the remaining claims as follows.

09/23/2003 AFORD1 00000001 500510 10051562

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<b>CERTIFICATE OF TRANSMISSION BY FACSIMILE (37 CFR 1.8)</b>			Docket No. <b>YO998426DIV</b>
Applicant(s): Chan et al.			
Serial No. <b>10/051,562</b>	Filing Date <b>January 18, 2002</b>	Examiner <b>Novacek, Christy L.</b>	Group Art Unit <b>2822</b>
Invention: <b>SELF-ALIGNED COUPLE-GATE MOSFET BY SELECTIVE EPITAXY AND SILICON WAFER BONDING TECHNIQUES</b>			
<p>I hereby certify that this <u>Amendment Under 37 C.F.R. 1.116</u> (Identify type of correspondence) is being facsimile transmitted to the United States Patent and Trademark Office (Fax. No. <u>703-872-9319</u>) on <u>September 23, 2003</u> (Date)</p> <p><u>Frederick W. Gibb, III</u> (Typed or Printed Name of Person Signing Certificate)  (Signature)</p> <p><b>OFFICIAL</b></p> <p>Note: Each paper must have its own certificate of mailing.</p> <p><b>RECEIVED</b> <b>CENTRAL FAX CENTER</b> <b>SEP 25 2003</b></p>			

P18/REV01